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LF353

SLOS012C - MARCH 1987-REVISED MARCH 2016

LF353 Wide-Bandwidth JFET-Input Dual Operational Amplifier

Technical

Documents

Features 1

- Low Input Bias Current 50 pA Typical
- Low Input Noise Current 0.01 pA/VHz Typical
- Low Supply Current 3.6 mA Typical
- High Input Impedance $10^{12} \Omega$ Typical
- Internally-Trimmed Offset Voltage
- Gain Bandwidth 3 MHz Typical
- High Slew Rate 13 V/µs Typical •

2 Applications

- Motor Integrated Systems: UPS
- Drives and Control Solutions: AC Inverter and VF Drives
- Renewables: Solar Inverters
- **Pro Audio Mixers**
- Oscilloscopes

3 Description

This LF353 device is a low-cost, high-speed, JFETinput operational amplifier with very low input offset voltage. It requires low supply current yet maintains a large gain-bandwidth product and a fast slew rate. In addition, the matched high-voltage JFET input provides very low input bias and offset currents.

The LF353 can be used in applications such as highspeed integrators, digital-to-analog converters. sample-and-hold circuits, and many other circuits.

The LF353 is characterized for operation from 0°C to 70°C.

Device Information⁽¹⁾

		=
PART NUMBER	PACKAGE	BODY SIZE (NOM)
LF353D	SOIC (8)	4.90 mm × 3.91 mm
LF353P	PDIP (8)	9.81 mm × 6.35 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

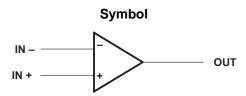




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (August 1994) to Revision C

Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and

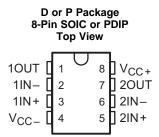
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5 Pin Configuration and Functions



Pin Functions

PIN		1/0	DESCRIPTION
NAME	NO.	I/O	DESCRIPTION
1OUT	1	0	Output
1IN-	2	I	Inverting input
1IN+	3	I	Noninverting input
V _{CC-}	4	—	Negative supply voltage
2IN+	5	I	Noninverting input
2IN-	6	I	Inverting input
20UT	7	0	Output
V _{CC+}	8	_	Positive supply voltage

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC+}	Supply voltage		18	V
V _{CC} -	Supply voltage		-18	V
VID	Differential input voltage		±30	V
VI	Input voltage ⁽²⁾		±15	V
	Duration of output short circuit	Unlir	nited	s
	Continuous total power dissipation		500	mW
	Lead temperature 1.6 mm (1/16 inch) from case for 10 s		260	°C
TJ	Junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.

6.2 ESD Ratings

				VALUE	UNIT
,	V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{CC+}	Supply voltage	3.5	18	V
V _{CC} -	Supply voltage	-3.5	-18	V
V _{CM}	Common-mode voltage	$V_{CC-} + 4$	$V_{CC+} - 4$	V
T _A	Operating temperature	0	70	°C

6.4 Thermal Information

		LF	353	
	THERMAL METRIC ⁽¹⁾	D (SOIC)	P (PDIP)	UNIT
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	106.6	55.1	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	51.5	45	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	46.5	32.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9.8	22.6	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	46.1	32.2	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

 $T_A = 0^{\circ}C$ to 70°C, $V_{CC+} = \pm 15 V$ (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
V _{IO}	Input offset voltage	V _{IC} = 0, R _S = 10 kΩ	$T_A = 25^{\circ}C$		5	10	mV
•10	input oneot voltage	ν ₁₀ = 0, ng = 10 mz	Full range ⁽¹⁾			13	
α_{VIO}	Average temperature coefficient of inputs offset voltage	$V_{IC}=0,\ R_S=10\ k\Omega$			10		µV/°C
	Input offset current ⁽²⁾	V – 0	$T_A = 25^{\circ}C$		25	100	pА
IIO		$V_{IC} = 0$	$T_A = 70^{\circ}C$			4	nA
Landthing automat(2)		nput bias current ⁽²⁾ $V_{IC} = 0$			50	200	pА
I _{IB}	input bias current ?	$V_{IC} = 0$	$T_A = 70^{\circ}C$			8	nA
V	Common-mode input voltage	Lower limit of range		-11	-12		V
VICR	range	Upper limit of range		11	15		v
V _{OM}	Maximum peak output voltage swing	$R_L = 10 \ k\Omega$		±12	±13.5		V
•	Large signal differential values		$T_A = 25^{\circ}C$	25	100		V/mV
A _{VD}	Large-signal differential voltage	$V_0 = \pm 10 \text{ V}, \text{ R}_L = 2 \text{ k}\Omega$	15			V/IIIV	
r _i	Input resistance	$T_J = 25^{\circ}C$	·		10 ¹²		Ω
CMRR	Common-mode rejection ratio	R _S ≤ 10 kΩ		70	100		dB
k _{SVR}	Supply-voltage rejection ratio	See ⁽³⁾	70	100		dB	
I _{CC}	Supply current				3.6	6.5	mA

(1) Full range is 0°C to 70°C

(2) Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperatures as close to the ambient temperature as possible.

(3) Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

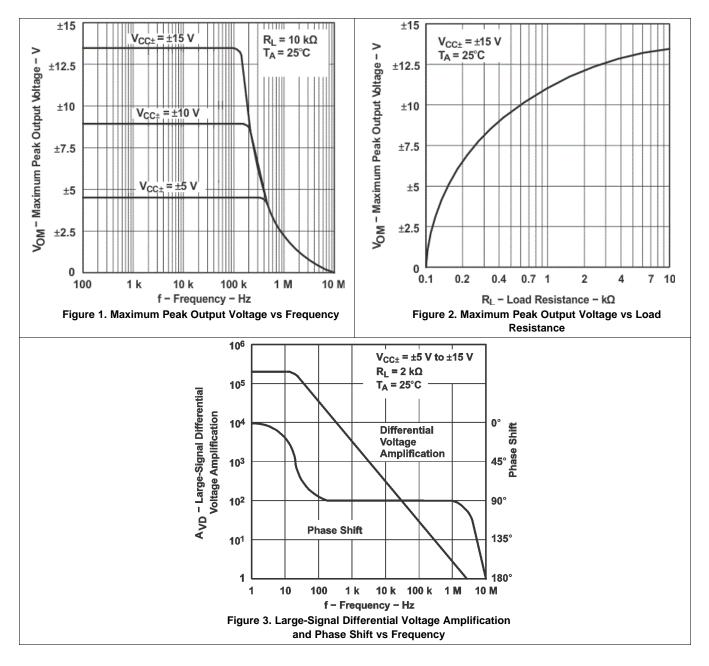
6.6 Switching Characteristics

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C}$, over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V ₀₁ /V ₀₂	Crosstalk attenuation	f = 1 kHz		120		dB
SR	Slew rate		8	13		V/µs
B1	Unity-gain bandwidth			3		MHz
V _n	Equivalent input noise voltage	$f = 1 \text{ kHz}, R_S = 20 \Omega$		18		nV/√Hz
l _n	Equivalent input noise current	f = 1 kHz		0.01		pA/√Hz

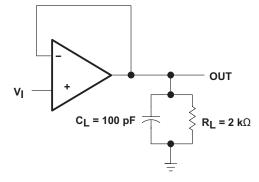


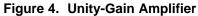
6.7 Typical Characteristics





7 Parameter Measurement Information





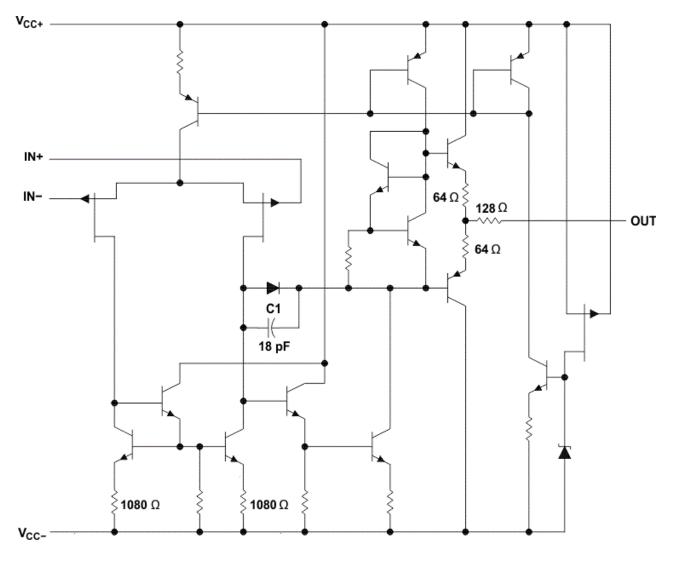


8 Detailed Description

8.1 Overview

The LF353 device is a JFET-input operational amplifier with low input bias and offset currents and fast slew rate. Each amplifier features JFET inputs (for high input impedance) coupled with bipolar output stages integrated on a single monolithic chip. The output is protected against shorts due to the resistive $200-\Omega$ output impedance.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 13-V/µs slew rate.

8.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LF353 has two independent amplifiers that have very low input bias current which allow using higher resistance resistors in the feedback network. The upper input common mode range goes to the upper supply rail. The lower common mode range does not include the negative supply rail. Output resistance is 200 ohms to protect the device from accidental shorts.

9.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage. In the same manner, it also makes negative voltages positive.

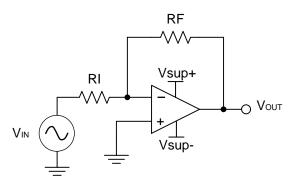


Figure 5. Inverting Amplifier

9.2.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application scales a signal of ± 0.5 V to ± 1.8 V. Setting the supply at ± 12 V is sufficient to accommodate this application.

9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using Equation 1 and Equation 2.

$$A_{V} = \frac{VOUT}{VIN}$$
(1)
$$A_{V} = \frac{1.8}{-0.5} = -3.6$$
(2)

Once the desired gain is determined, choose a value for RI or RF. Choosing a value in the k Ω range is desirable because the amplifier circuit uses currents in the mA range. This ensures the part does draw too much current. For this example, choose 10 k Ω for RI and 36 k Ω for RF, as shown in Equation 3.

$$A_{V} = -\frac{RF}{RI}$$
(3)



Typical Application (continued)

9.2.3 Application Curve

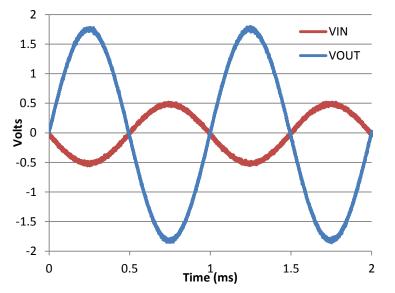


Figure 6. Input and Output Voltages of the Inverting Amplifier

10 Power Supply Recommendations

CAUTION

Supply voltages larger than 36 V for a single-supply or outside the range of ± 18 V for a dual-supply can permanently damage the device (see the *Absolute Maximum Ratings*).

Place 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or highimpedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout Example*.

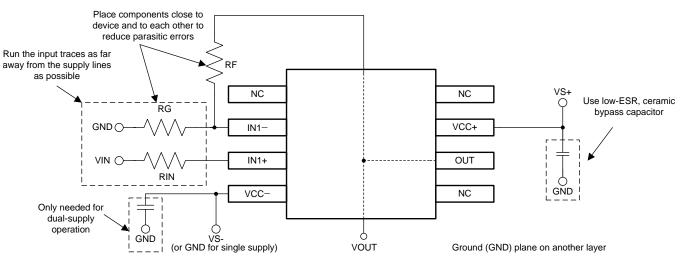


11 Layout

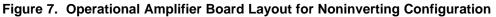
11.1 Layout Guidelines

For best operational performance of the device, use the following layout guidelines:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the
 operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance
 power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques* (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in *Layout Example*.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.



11.2 Layout Example



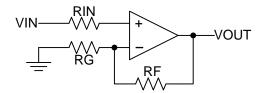


Figure 8. Operational Amplifier Schematic for Noninverting Configuration

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see Circuit Board Layout Techniques (SLOA089).

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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12.3 Trademarks

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12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LF353D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LF353	Samples
LF353DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LF353	Samples
LF353DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LF353	Samples
LF353DRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LF353	Samples
LF353DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	LF353	Samples
LF353P	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	LF353P	Samples
LF353PE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	0 to 70	LF353P	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

16-Jan-2016

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LF353DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LF353DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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PACKAGE MATERIALS INFORMATION

16-Jan-2016



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LF353DR	SOIC	D	8	2500	367.0	367.0	35.0
LF353DR	SOIC	D	8	2500	340.5	338.1	20.6

P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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